

# PSMN1R8-30PL

# N-channel 30 V, 1.8 m $\Omega$ logic level MOSFET in TO-220 Rev. 02 — 2 November 2010 Product of

**Product data sheet** 

#### 1. **Product profile**

### 1.1 General description

Logic level N-channel MOSFET in TO-220 package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

### 1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for logic level gate drive sources

### 1.3 Applications

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	30	V
I <sub>D</sub>	drain current	$T_{mb}$ = 25 °C; $V_{GS}$ = 10 V; see Figure 1	[1]	-	-	100	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	-	270	W
Tj	junction temperature			-55	-	175	°C
Static char	racteristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 12}{\text{Figure } 12};$	[2]	-	1.6	1.8	mΩ
Dynamic c	haracteristics						
$Q_{GD}$	gate-drain charge	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A};$		-	22	-	nC
Q <sub>G(tot)</sub>	total gate charge	V <sub>DS</sub> = 15 V; see <u>Figure 14;</u> see <u>Figure 15</u>		-	83	-	nC
Avalanche	ruggedness						
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$\begin{split} &V_{GS} = 10 \text{ V; } T_{j(init)} = 25 \text{ °C;} \\ &I_D = 100 \text{ A; } V_{sup} \leq 30 \text{ V;} \\ &R_{GS} = 50  \Omega; \text{ unclamped} \end{split}$		-	-	1.1	J

<sup>[1]</sup> Continuous current is limited by package.



<sup>[2]</sup> Measured 3 mm from package.

# 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain	mb	D
3	S	source		<sub>G</sub> (EA)
mb	D	mounting base; connected to drain	1 2 3	mbb076 S
			SOT78 (TO-220AB)	

# 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN1R8-30PL	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

# 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		· · · · · · · · · · · · · · · · · · ·				
Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$		-	30	V
$V_{DGR}$	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$		-	30	V
$V_{GS}$	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 100 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{ of } \text{ of }  o$	<u>[1]</u>	-	100	Α
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; see <u>Figure 1</u>	<u>[1]</u>	-	100	Α
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25  ^{\circ}C$ ; see <u>Figure 3</u>		-	1120	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	270	W
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drain o	diode					
Is	source current	T <sub>mb</sub> = 25 °C	<u>[1]</u>	-	100	Α
I <sub>SM</sub>	peak source current	pulsed; t <sub>p</sub> ≤ 10 µs; T <sub>mb</sub> = 25 °C		-	1120	Α
Avalanche rug	gedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 100 A; $V_{sup} \le$ 30 V; $R_{GS}$ = 50 $\Omega$ ; unclamped		-	1.1	J

### [1] Continuous current is limited by package.

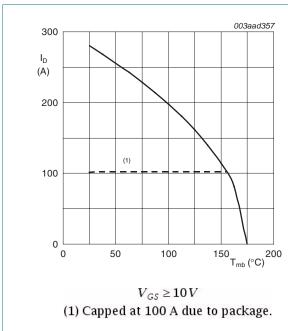


Fig 1. Continuous drain current as a function of mounting base temperature

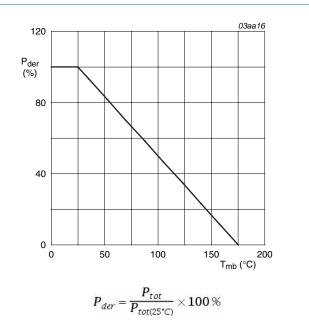
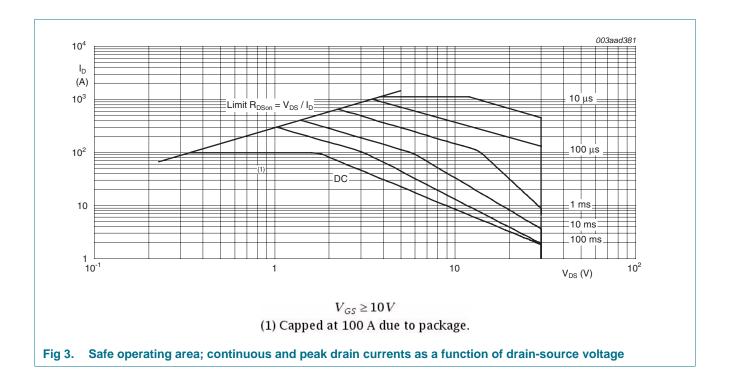


Fig 2. Normalized total power dissipation as a function of mounting base temperature



### 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	0.3	0.56	K/W

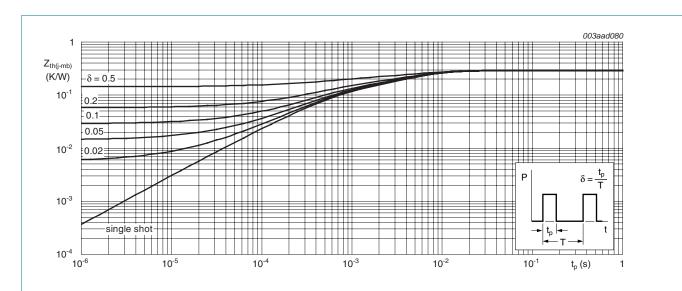


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration; typical values

# 6. Characteristics

Table 6. Characteristics

Tested to JEDEC standards where applicable.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	30	-	-	V
	voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	27	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}$ ; $V_{DS} = V_{GS}$ ; $T_j = 25 \text{ °C}$ ; see <u>Figure 10</u> ; see <u>Figure 11</u>	1.3	1.7	2.15	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = 175$ °C; see Figure 11	0.5	-	-	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = -55$ °C; see Figure 11	-	-	2.45	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.3	4	μΑ
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ °C}$	-	-	200	μΑ
$I_{GSS}$	gate leakage current	$V_{GS} = 16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
		$V_{GS} = -16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see <u>Figure 12</u>	-	1.8	2.3	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 ^{\circ}\text{C};$ see Figure 13	-	-	3.42	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 100 ^{\circ}\text{C};$ see <u>Figure 13</u>	-	-	2.4	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 175 ^{\circ}\text{C};$ see <u>Figure 13</u>	-	-	4.73	mΩ
		$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 25 °C; see <u>Figure 13</u> ; see <u>Figure 12</u>	[1] -	1.6	1.8	mΩ
$R_G$	gate resistance	f = 1 MHz	-	1	-	Ω
Dynamic ch	aracteristics					
$Q_{G(tot)}$	total gate charge	$I_D = 25 \text{ A}$ ; $V_{DS} = 15 \text{ V}$ ; $V_{GS} = 10 \text{ V}$ ; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	170	-	nC
		$I_D = 0 A; V_{DS} = 0 V; V_{GS} = 10 V$	-	158	-	nC
		$I_D = 25 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$	-	83	-	nC
$Q_{GS}$	gate-source charge	see <u>Figure 14</u> ; see <u>Figure 15</u>	-	29	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate-source charge		-	17	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate-source charge		-	12	-	nC
$Q_{GD}$	gate-drain charge		-	22	-	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	V <sub>DS</sub> = 15 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	2.6	-	V
C <sub>iss</sub>	input capacitance	$V_{DS} = 12 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	10180	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; see <u>Figure 16</u>	-	2000	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	872	-	pF

 Table 6.
 Characteristics ...continued

Tested to JEDEC standards where applicable.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$t_{d(on)}$	turn-on delay time	$V_{DS} = 12 \text{ V}; R_L = 0.5 \Omega; V_{GS} = 4.5 \text{ V};$	-	92	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 4.7 \Omega$	-	156	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	135	-	ns
t <sub>f</sub>	fall time		-	69	-	ns
Source-dra	in diode					
$V_{SD}$	source-drain voltage	$I_S = 25 \text{ A}$ ; $V_{GS} = 0 \text{ V}$ ; $T_j = 25 \text{ °C}$ ; see <u>Figure 17</u>	-	0.7	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 30 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$	-	64	-	ns
Q <sub>r</sub>	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 12 \text{ V}$	-	60	-	nC

### [1] Measured 3 mm from package.

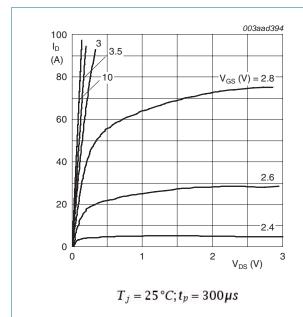


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

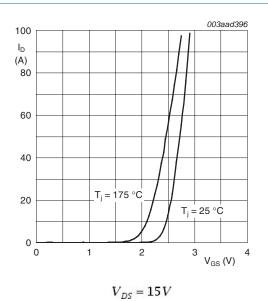


Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values

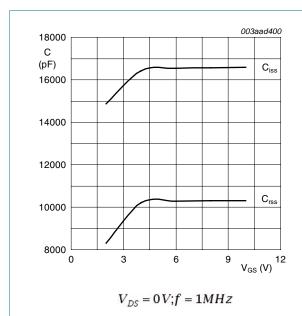


Fig 7. Input and reverse transfer capacitances as a function of gate-source voltage; typical values

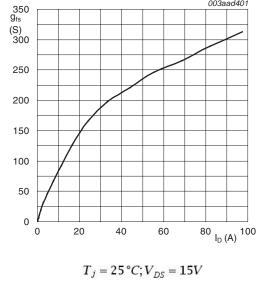
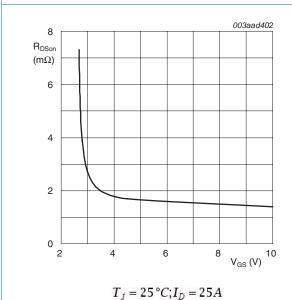
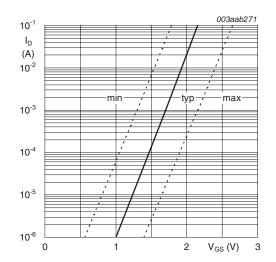


Fig 8. Forward transconductance as a function of drain current; typical values



Drain-source on-state resistance as a function Fig 9.

of gate-source voltage; typical values



$$T_j = 25 \,{}^{\circ}C; V_{DS} = 5V$$

Fig 10. Sub-threshold drain current as a function of gate-source voltage

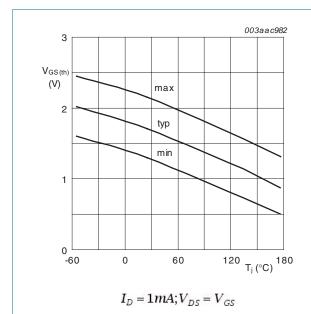


Fig 11. Gate-source threshold voltage as a function of junction temperature

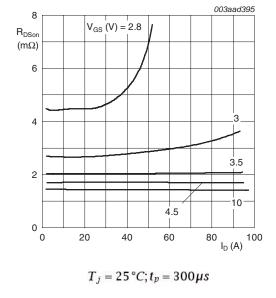


Fig 12. Drain-source on-state resistance as a function of drain current; typical values

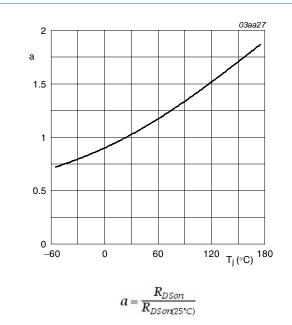


Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature

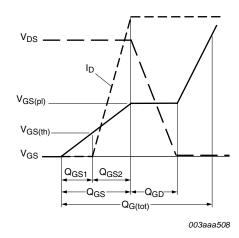
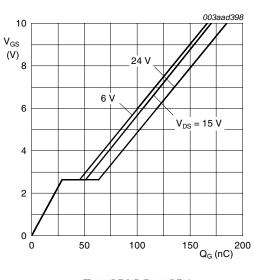
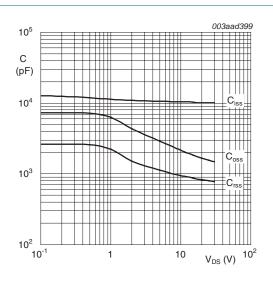


Fig 14. Gate charge waveform definitions



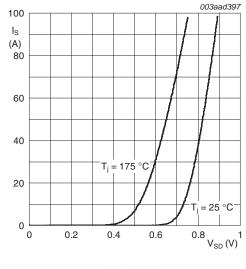
 $T_j = 25 \,^{\circ}C; I_D = 25A$ 

Fig 15. Gate-source voltage as a function of gate charge; typical values



$$V_{GS} = 0V; f = 1MHz$$

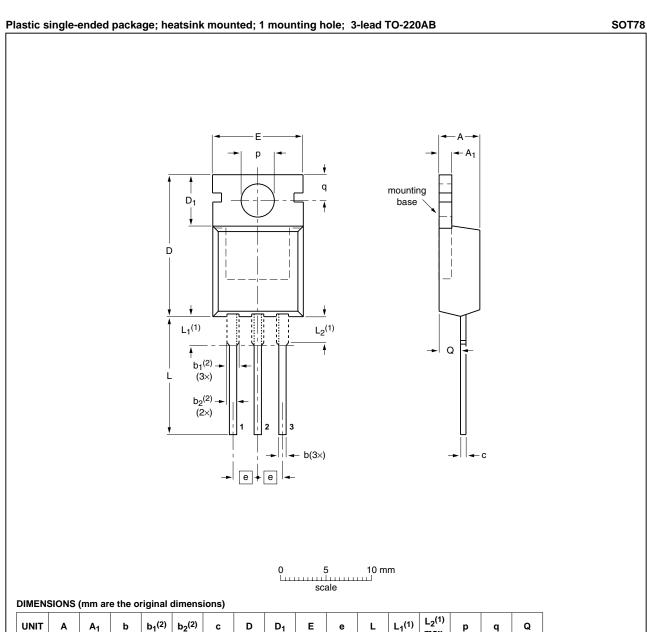
Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



 $V_{GS} = 0V$ 

Fig 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

# 7. Package outline



UN	T A	A <sub>1</sub>	b	b <sub>1</sub> (2)	b <sub>2</sub> (2)	С	D	D <sub>1</sub>	E	е	L	L <sub>1</sub> (1)	L <sub>2</sub> <sup>(1)</sup> max.	р	q	Q	
mn	n 4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2	

#### Notes

- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE		REFER	ENCES		EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT78		3-lead TO-220AB	SC-46			<del>08-04-23</del> 08-06-13	

Fig 18. Package outline SOT78 (TO-220AB)

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# 8. Revision history

### Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN1R8-30PL v.2	20101102	Product data sheet	-	PSMN1R8-30PL v.1
Modifications:				
	<ul> <li>Various change</li> </ul>	es to content.		
PSMN1R8-30PL v.1	20100218	Objective data sheet	-	-

### 9. Legal information

#### 9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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# PSMN1R8-30PL

# **Nexperia**

N-channel 30 V, 1.8 m $\Omega$  logic level MOSFET in TO-220

# 11. Contents

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Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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